



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Features

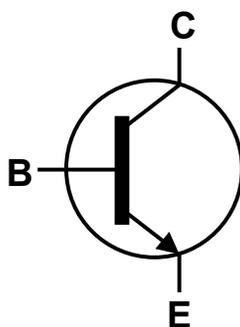
- Epitaxial Planar Die Construction
- Low Saturation Voltage $V_{CE(sat)} < 300\text{mV @ } 150\text{mA}$
- Complementary PNP Type: NK-MMBT2907A
- Ideal for Low Power Amplification and Switching

Mechanical Data

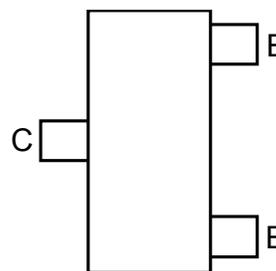
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208 
- Weight: 0.008 grams (Approximate)



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	600	mA
Peak Pulse Collector Current (single pulse)	I_{CM}	800	mA
Peak Pulse Base Current	I_{BM}	200	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

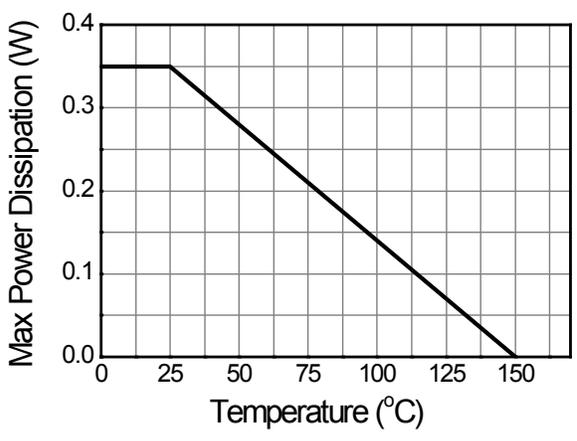
Characteristic	Symbol	Value	Unit
Collector Power Dissipation	P_D	(Note 5)	310
		(Note 6)	350
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	(Note 5)	403
		(Note 6)	357
Thermal Resistance, Junction to Leads	$R_{\theta JL}$	350	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings (Note 8)

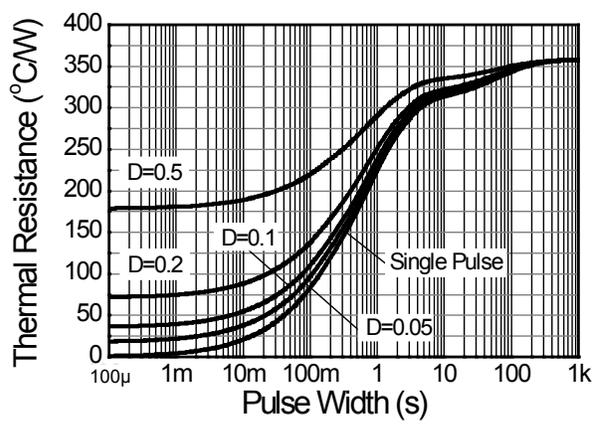
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is mounted on 15 mm x 15mm 1oz copper.
 - Thermal resistance from junction to solder-point (at the end of the leads).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

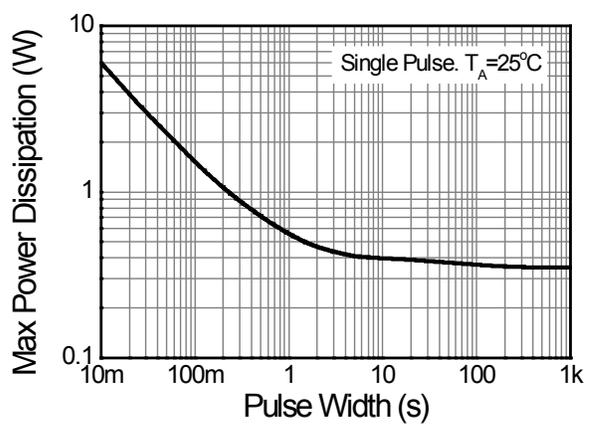
Thermal Characteristics and Derating Information



Derating Curve



Transient Thermal Impedance

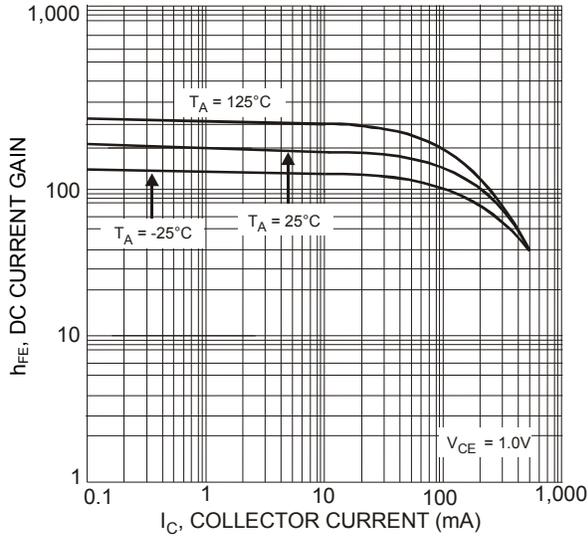


Pulse Power Dissipation

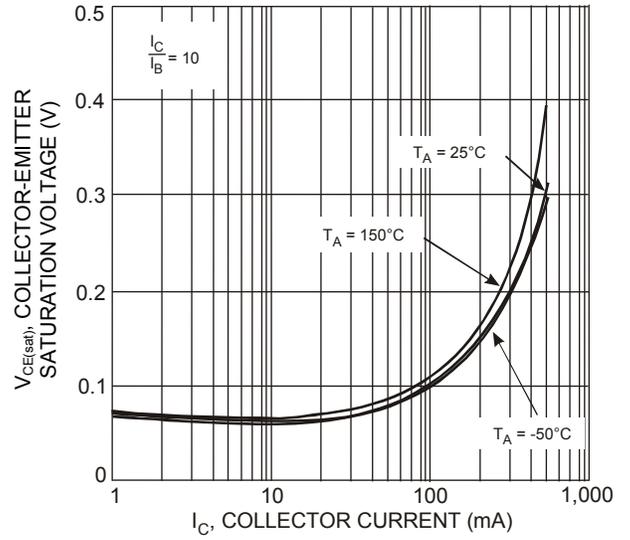
Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV_{CBO}	75	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	40	—	V	$I_C = 10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	—	V	$I_E = 100\mu\text{A}, I_C = 0$
Collector Cut-Off Current	I_{CBO}	—	10	nA μA	$V_{CB} = 60\text{V}, I_E = 0$ $V_{CB} = 60\text{V}, I_E = 0, T_A = +150^\circ\text{C}$
Collector Cut-Off Current	I_{CEX}	—	10	nA	$V_{CE} = 60\text{V}, V_{EB(\text{off})} = 3.0\text{V}$
Collector Cut-Off Current	I_{CEV}	—	10	nA	$V_{CE} = 60\text{V}, V_{BE} = \pm 0.25\text{V}$
Emitter Cut-Off Current	I_{EBO}	—	10	nA	$V_{EB} = 5.0\text{V}, I_C = 0$
Base Cut-Off Current	I_{BL}	—	20	nA	$V_{CE} = 60\text{V}, V_{EB(\text{off})} = 3.0\text{V}$
ON CHARACTERISTICS (Note 9)					
DC Current Gain	h_{FE}	35 50 75 100 40 50 35	— — — 300 — — —	—	$I_C = 100\mu\text{A}, V_{CE} = 10\text{V}$ $I_C = 1.0\text{mA}, V_{CE} = 10\text{V}$ $I_C = 10\text{mA}, V_{CE} = 10\text{V}$ $I_C = 150\text{mA}, V_{CE} = 10\text{V}$ $I_C = 500\text{mA}, V_{CE} = 10\text{V}$ $I_C = 10\text{mA}, V_{CE} = 10\text{V}, T_A = -55^\circ\text{C}$ $I_C = 150\text{mA}, V_{CE} = 1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(\text{sat})}$	—	0.3 1.0	V	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(\text{sat})}$	0.6 —	1.2 2.0	V	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	8	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	—	25	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Transition frequency	f_T	300	—	MHz	$V_{CE} = 20\text{V}, I_C = 20\text{mA}, f = 100\text{MHz}$
Noise Figure	N_F	—	4.0	dB	$V_{CE} = 10\text{V}, I_C = 100\mu\text{A}, R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	10	ns	$V_{CC} = 30\text{V}, I_C = 150\text{mA}, V_{BE(\text{off})} = -0.5\text{V}, I_{B1} = 15\text{mA}$
Rise Time	t_r	—	25	ns	$V_{CC} = 30\text{V}, I_C = 150\text{mA}, I_{B1} = 15\text{mA}, V_{BE(\text{off})} = 0.5\text{V}$
Storage Time	t_s	—	225	ns	$V_{CC} = 30\text{V}, I_C = 150\text{mA}, I_{B1} = -I_{B2} = 15\text{mA}$
Fall Time	t_f	—	60	ns	$V_{CC} = 30\text{V}, I_C = 150\text{mA}, I_{B1} = -I_{B2} = 15\text{mA}$

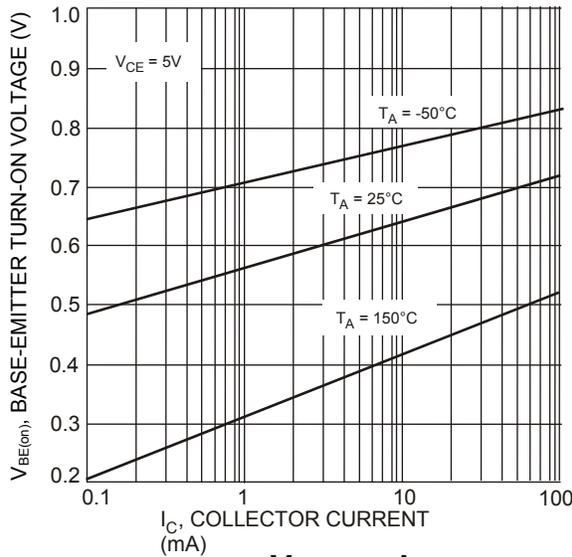
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.



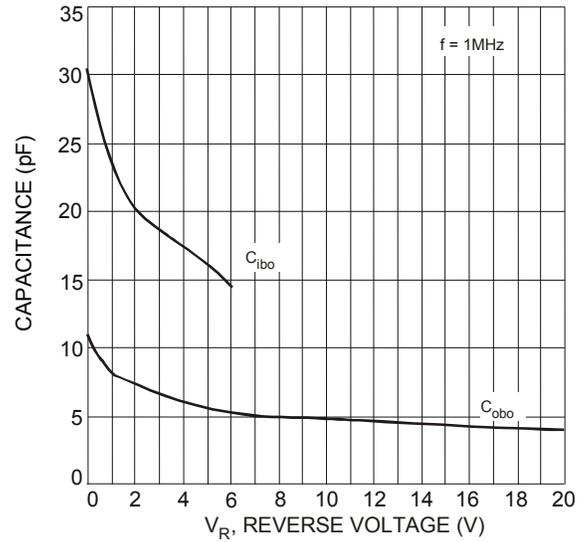
$h_{FE} v I_C$



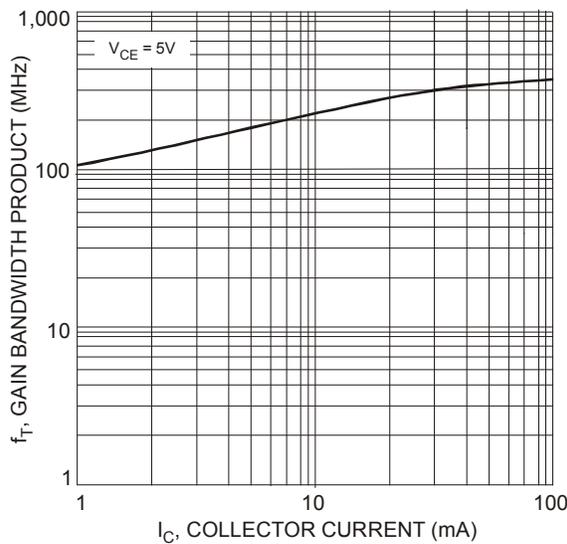
$V_{CE(sat)} v I_C$



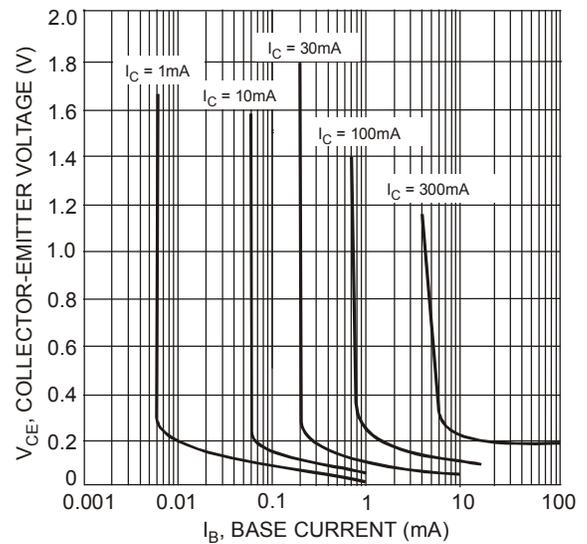
$V_{BE(on)} v I_C$



$C v V_R$



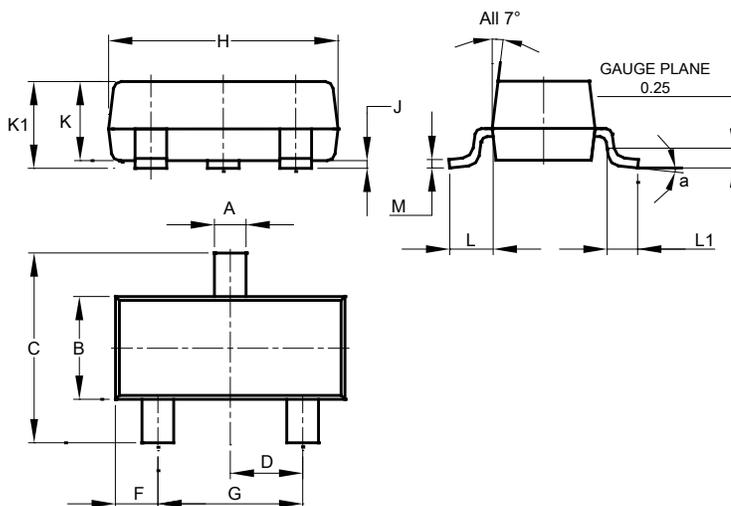
$f_T v I_C$



$V_{CE} v I_B$

Package Outline Dimensions

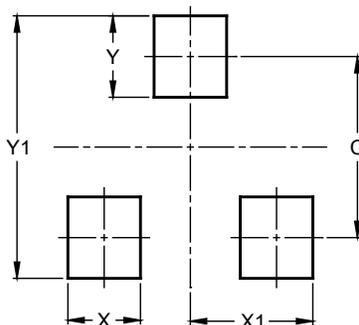
SOT23



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9